



45V PNP SMALL-SIGNAL TRANSISTOR IN DFN1110-3/SWP

Description

The BC807-40FHWQ bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BVcEo > -45V
- I_C = -500mA Continuous Collector Current
- Low-Profile, 0.6mm-High Package for Thin Applications
- Sidewall Tin Plating for Wettable Flanks in AOI
- Complementary NPN Type: BC817-40FHWQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The BC807-40FHWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: U-DFN1110-3/SWP
- Package Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.001714 grams (Approximate)

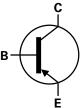
Application

• Switching and amplification

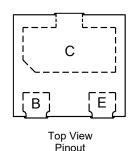
U-DFN1110-3/SWP (Type A)



Bottom View



Device Symbol



Ordering Information (Note 4)

| Orderable Part Number | mhay Dackaga Mayking | | Deal Size (inches) | Tone Width (mm) | Packing | |
|-----------------------|--------------------------|---------|--------------------|-----------------|---------|---------|
| Orderable Part Number | Package | Marking | Reel Size (inches) | Tape Width (mm) | Qty. | Carrier |
| BC807-40FHWQ-7 | U-DFN1110-3/SWP (Type A) | 2V8 | 7 | 8 | 5000 | Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

U-DFN1110-3/SWP (Type A)



ABC = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 5 = 2025) WW = Week Code 01 to 53



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | Vсво | -50 | V |
| Collector-Emitter Voltage | V _{CEO} | -45 | V |
| Emitter-Base Voltage | VEBO | -7 | V |
| Continuous Collector Current | Ic | -500 | mA |
| Peak Pulse Collector Current | Ісм | -1 | Α |
| Peak Base Current | Івм | -200 | mA |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|---|-----------------------------------|----------------|------|------|
| Power Dissipation | (Note 5) | P _D | 460 | mW |
| Thermal Resistance, Junction to Ambient | (Note 5) | Reja | 272 | °C/W |
| Thermal Resistance, Junction to Case (Note 6) | | Rejc | 81 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C | |

ESD Ratings (Note 7)

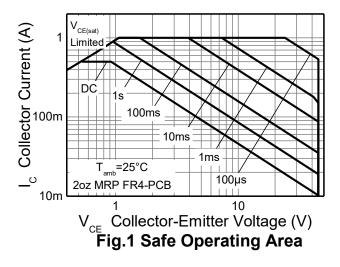
| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge – Human Body Model | ESD HBM | 4000 | V | 3A |
| Electrostatic Discharge – Charged Device Model | ESD CDM | 1000 | V | C3 |

Notes:

- 5. For a device mounted with the exposed collector pads on minimum recommended pad layout and 2oz. copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Thermal resistance from junction to the top of the case.
- 7. Refer to JEDEC specifications JESD22-A114 and JESD22-C101.



Thermal Characteristics and Derating Information



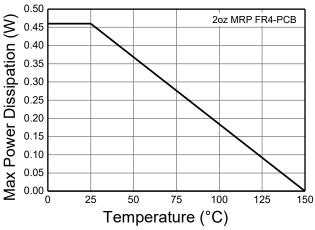


Fig.2 Derating Curve

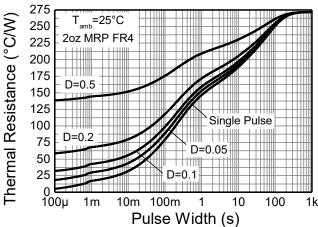


Fig.3 Transient Thermal Impedance

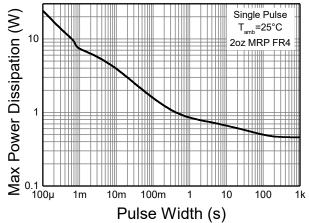


Fig.4 Pulse Power Dissipation

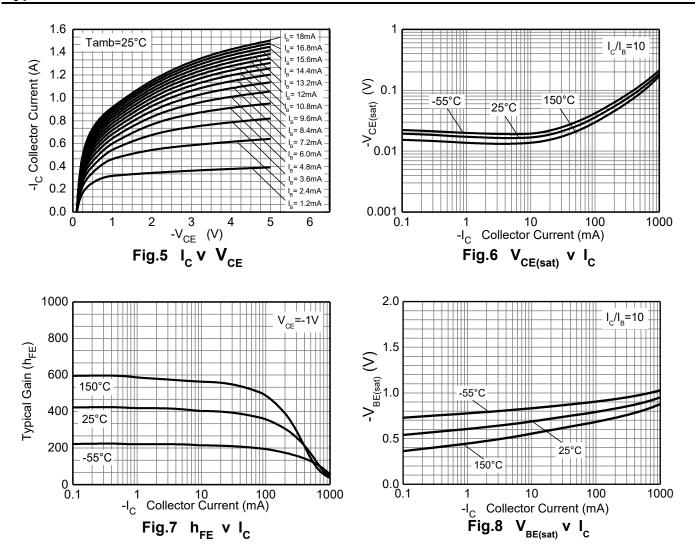


Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Conditions |
|---|---------------------|-----|-----|------|------|--|
| Collector-Base Breakdown Voltage | ВУсво | -50 | _ | _ | V | I _C = -100μA |
| Collector-Emitter Breakdown Voltage (Note 8) | BVceo | -45 | _ | _ | V | Ic = -10mA |
| Emitter-Base Breakdown Voltage | BV _{EBO} | -7 | _ | _ | V | I _E = -100μA |
| Collector-Base Cutoff Current | lana | _ | _ | -100 | nA | $V_{CB} = -20V, I_{E} = 0$ |
| Collector-Base Cuton Current | Ісво | _ | _ | -5 | μΑ | $V_{CB} = -20V$, $I_E = 0$, $T_J = +150$ °C |
| Emitter-Base Cutoff Current | I _{EBO} | _ | _ | -100 | nA | $V_{EB} = -5.6V, I_{C} = 0$ |
| DC Current Gain (Note 8) | hFE | 250 | _ | 600 | _ | $V_{CE} = -1V$, $I_{C} = -100$ mA |
| DC Current Gain (Note 8) | | 40 | _ | _ | | V _{CE} =- 1V, I _C = -500mA |
| Collector-Emitter Saturation Voltage (Note 8) | VcE(sat) | _ | _ | -700 | mV | I _C = -500mA, I _B = -50mA |
| Base-Emitter Turn-On Voltage (Note 8) | V _{BE(on)} | _ | _ | -1.2 | V | V _{CE} = -1V, I _C = -500mA |
| Transition Frequency | fτ | 80 | _ | _ | MHz | V _{CE} = -5V, I _C = -10mA, f = 100MHz |
| Collector-Base Capacitance | C_{cbo} | _ | _ | 12 | pF | V _{CB} = -10V, f = 1MHz |

Note: 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

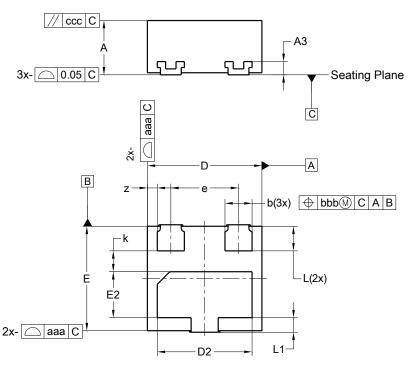




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1110-3/SWP (Type A)



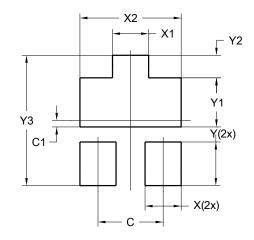
| U-DFN1110-3/SWP | | | | | |
|----------------------|----------|------|-------|--|--|
| (Type A) | | | | | |
| Dim | Min | Max | Тур | | |
| Α | 0.47 | 0.57 | 0.52 | | |
| A1 | 0.00 | 0.05 | 0.03 | | |
| A3 | - | _ | 0.127 | | |
| b | 0.22 | 0.30 | 0.26 | | |
| D | 1.05 | 1.15 | 1.10 | | |
| D2 | 0.87 | 0.95 | 0.91 | | |
| е | 0.65 BSC | | | | |
| Е | 0.95 | 1.05 | 1.00 | | |
| E2 | 0.40 | 0.48 | 0.44 | | |
| k | - | _ | 0.20 | | |
| L | 0.20 | 0.27 | 0.23 | | |
| L1 | 0.09 | 0.19 | 0.14 | | |
| Z | 0.095 | | | | |
| aaa | 0.25 | | | | |
| bbb | 0.10 | | | | |
| ccc | 0.10 | | | | |
| All Dimensions in mm | | | | | |

Note: Side wall tin plated package for wettable flanks in AOI.

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1110-3/SWP (Type A)



| Dimensions | Value |
|------------|---------|
| Dimensions | (in mm) |
| С | 0.650 |
| C1 | 0.065 |
| X | 0.360 |
| X1 | 0.360 |
| X2 | 1.010 |
| Y | 0.435 |
| Y1 | 0.490 |
| Y2 | 0.225 |
| Y3 | 1.300 |



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